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Front Matter: Volume 7640

, "Front Matter: Volume 7640," Proc. SPIE 7640, Optical Microlithography XXIII, 764001 (16 April 2010); doi: 10.1117/12.862757

SPIE.

Event: SPIE Advanced Lithography, 2010, San Jose, California, United States

PROCEEDINGS OF SPIE

Optical Microlithography XXIII

Mircea V. Dusa
Will Conley
Editors

23–25 February 2010
San Jose, California, United States

Sponsored by
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SEMATECH Inc. (United States)

Published by
SPIE

Volume 7640
Part One of Two Parts

Proceedings of SPIE, 0277-786X, v. 7640

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Author(s), "Title of Paper," in *Optical Microlithography XXIII*, edited by Mircea V. Dusa, Will Conley, Proceedings of SPIE Vol. 7640 (SPIE, Bellingham, WA, 2010) Article CID Number.

ISSN 0277-786X

ISBN 9780819480545

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445

SPIE.org

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